



**THE DATASHEET OF
NVMFS5H663NLWFT1G**



MOSFET – Power, Single N-Channel

60 V, 7.2 mΩ, 67 A

NVMFS5H663NL, NVMFS5H663NLWF

NVMFS5H663NLWF - Wettable Flank Option for Enhanced Optical Inspection.

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Value	Unit	
V_{DSS}	Drain-to-Source Voltage		60	V	
V_{GS}	Gate-to-Source Voltage		± 20	V	
I_D	Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)	Steady State	$T_C = 25\text{ }^\circ\text{C}$	67	A
			$T_C = 100\text{ }^\circ\text{C}$	47	
P_D	Power Dissipation $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25\text{ }^\circ\text{C}$	63	W
			$T_C = 100\text{ }^\circ\text{C}$	31.3	
I_D	Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	Steady State	$T_A = 25\text{ }^\circ\text{C}$	16.2	A
			$T_A = 100\text{ }^\circ\text{C}$	11.4	
P_D	Power Dissipation $R_{\theta JA}$ (Notes 1 & 2)	Steady State	$T_A = 25\text{ }^\circ\text{C}$	3.7	W
			$T_A = 100\text{ }^\circ\text{C}$	1.8	
I_{DM}	Pulsed Drain Current	$T_A = 25\text{ }^\circ\text{C}, t_p = 10\text{ }\mu\text{s}$	359	A	
T_J, T_{stg}	Operating Junction and Storage Temperature		-55 to +175	$^\circ\text{C}$	
I_S	Source Current (Body Diode)		52	A	
E_{AS}	Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 3.8\text{ A}$)		274	mJ	
T_L	Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		260	$^\circ\text{C}$	

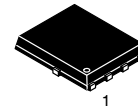
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

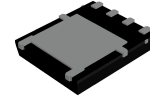
Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Junction-to-Case - Steady State	2.4	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Junction-to-Ambient - Steady State (Note 2)	41	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

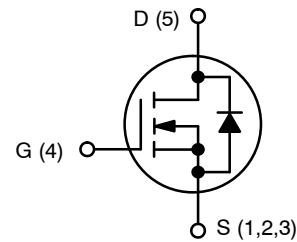
$V_{(BR)DSS}$	$R_{DS(ON)}\text{ MAX}$	$I_D\text{ MAX}$
60 V	7.2 mΩ @ 10 V	67 A
	10 mΩ @ 4.5 V	



**DFN5
(SO-8FL)
CASE 488AA
STYLE 1**

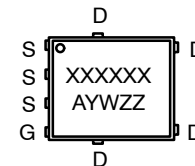


**DFNW5
CASE 507BA**



N-CHANNEL MOSFET

MARKING DIAGRAM



5H663L = (NVMFS5H663NL) or
663LWF = (NVMFS5H663NLWF)
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NVMFS5H663NL, NVMFS5H663NLWF

ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
$V_{(BR)DSS}/T_J$	Drain-to-Source Breakdown Voltage Temperature Coefficient			43		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{ V}, V_{DS} = 60\text{ V}$	$T_J = 25\text{ }^\circ\text{C}$		10	μA
			$T_J = 125\text{ }^\circ\text{C}$		250	
I_{GSS}	Gate-to-Source Leakage Current	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

ON CHARACTERISTICS (Note 4)

$V_{GS(TH)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 56\text{ }\mu\text{A}$	1.2		2.0	V
$V_{GS(TH)}/T_J$	Threshold Temperature Coefficient			-5.6		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Drain-to-Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		5.8	7.2	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		8	10	
g_{FS}	Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		64		S

CHARGES, CAPACITANCES & GATE RESISTANCE

C_{ISS}	Input Capacitance	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 30\text{ V}$		1131		pF
C_{OSS}	Output Capacitance			213		
C_{RSS}	Reverse Transfer Capacitance			7.5		
Q_{OSS}	Output Charge	$V_{GS} = 0\text{ V}, V_{DD} = 30\text{ V}$		18		nC
$Q_{G(TOT)}$	Total Gate Charge	$V_{GS} = 4.5\text{ V}, V_{DS} = 30\text{ V}; I_D = 20\text{ A}$		8		
$Q_{G(TOT)}$	Total Gate Charge	$V_{GS} = 10\text{ V}, V_{DS} = 30\text{ V}; I_D = 20\text{ A}$		17		
$Q_{G(TH)}$	Threshold Gate Charge	$V_{GS} = 4.5\text{ V}, V_{DS} = 30\text{ V}; I_D = 20\text{ A}$		2.2		
Q_{GS}	Gate-to-Source Charge			3.8		
Q_{GD}	Gate-to-Drain Charge			1.4		
V_{GP}	Plateau Voltage			3.1		V

SWITCHING CHARACTERISTICS (Note 5)

$t_{d(ON)}$	Turn-On Delay Time	$V_{GS} = 4.5\text{ V}, V_{DS} = 48\text{ V}, I_D = 20\text{ A}, R_G = 2.5\text{ }\Omega$		13.4		ns
t_r	Rise Time			52.7		
$t_{d(OFF)}$	Turn-Off Delay Time			26.2		
t_f	Fall Time			9.5		

DRAIN-SOURCE DIODE CHARACTERISTICS

V_{SD}	Forward Diode Voltage	$V_{GS} = 0\text{ V}, I_S = 20\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$		0.84	1.2	V
			$T_J = 125\text{ }^\circ\text{C}$		0.70		
t_{RR}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 20\text{ A}$		30.7		ns	
t_a	Charge Time			17.7			
t_b	Discharge Time			13.1			
Q_{RR}	Reverse Recovery Charge			22.8		nC	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

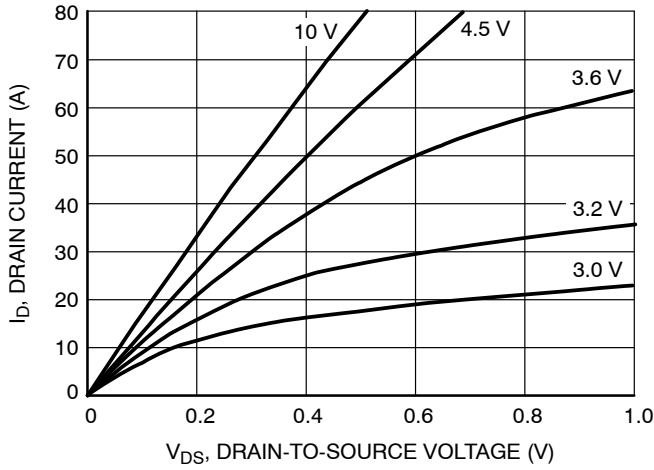


Figure 1. On-Region Characteristics

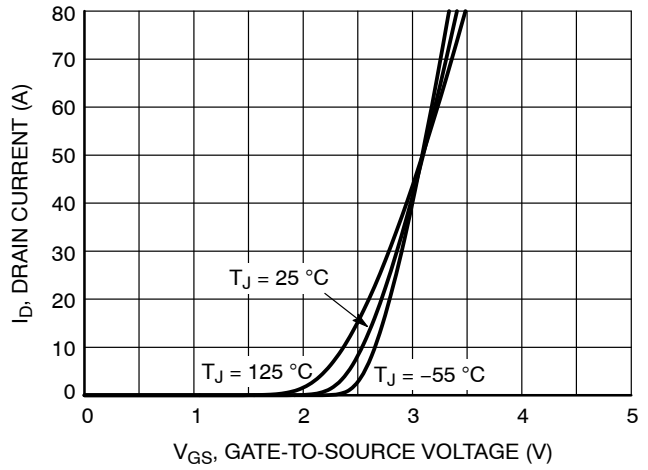


Figure 2. Transfer Characteristics

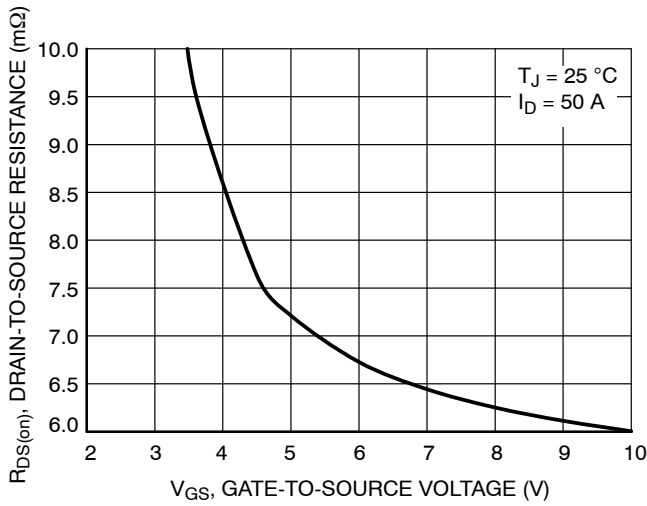


Figure 3. On-Resistance vs. Gate-to-Source Voltage

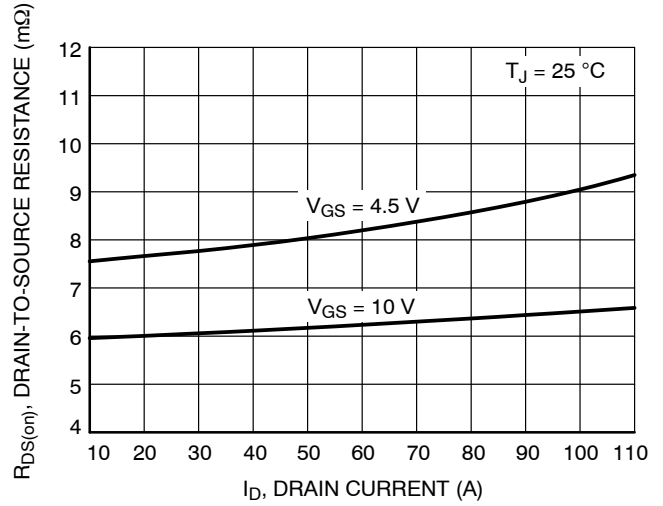


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

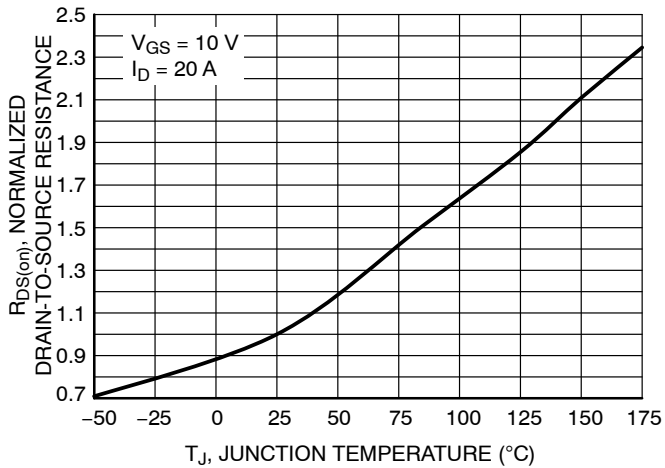


Figure 5. On-Resistance Variation with Temperature

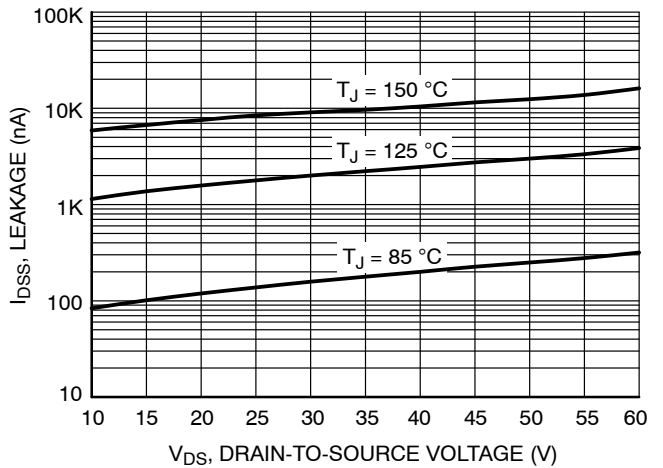


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS (continued)

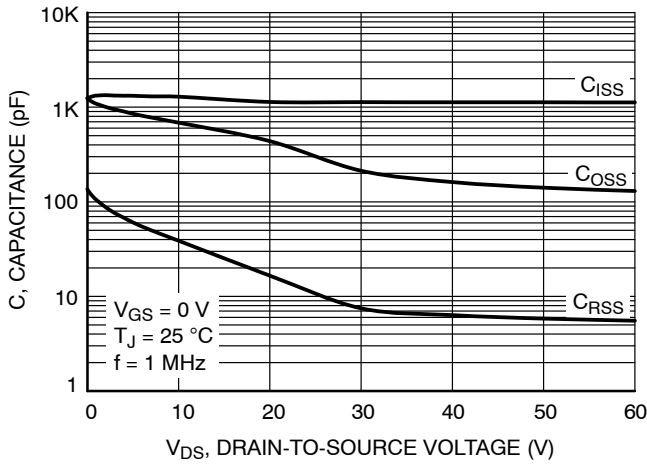


Figure 7. Capacitance Variation

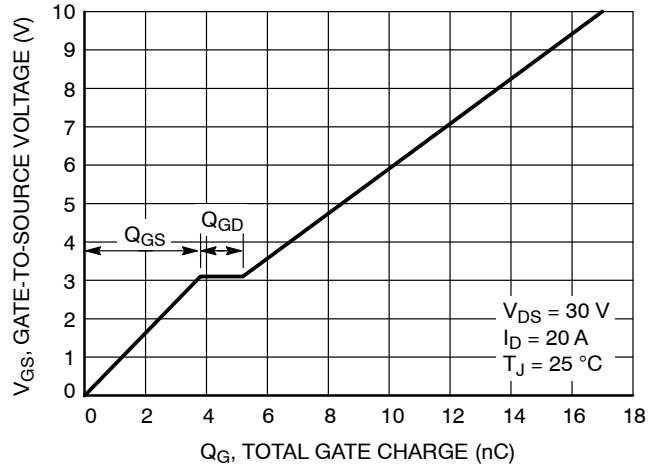


Figure 8. Gate-to-Source Voltage vs. Total Charge

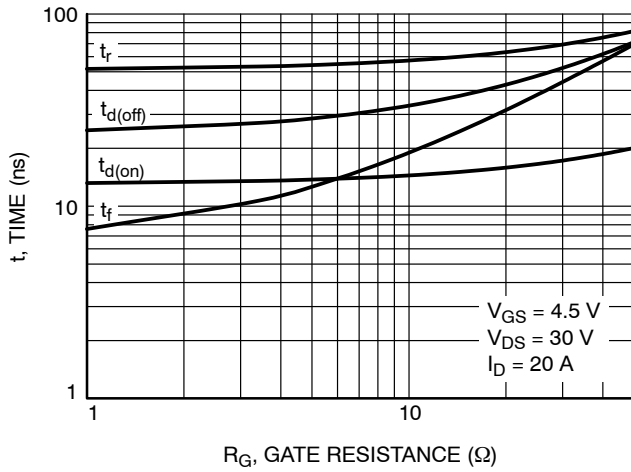


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

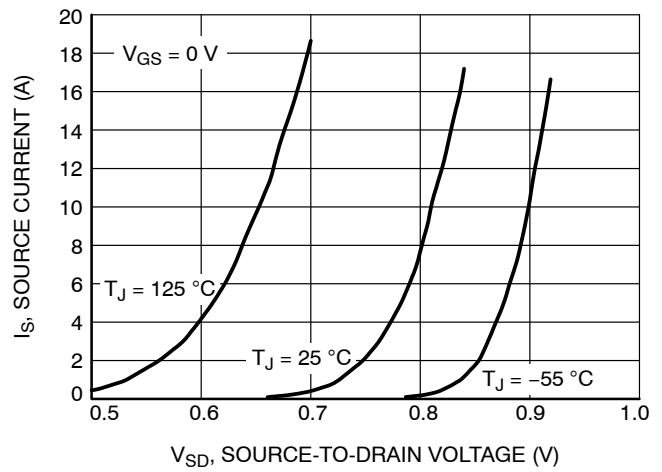


Figure 10. Diode Forward Voltage vs. Current

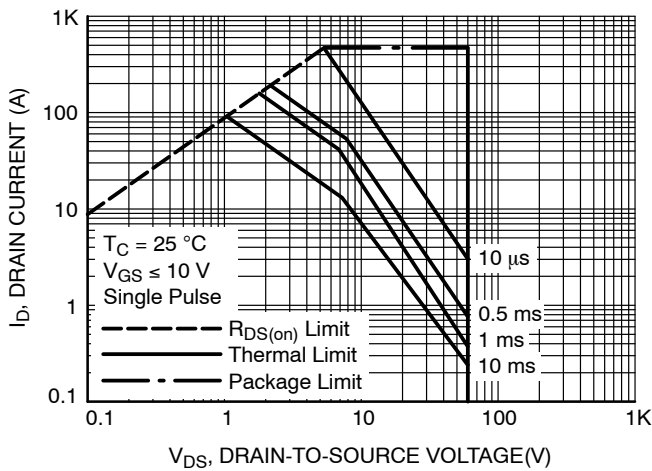


Figure 11. Maximum Rated Forward Biased Safe Operating Area

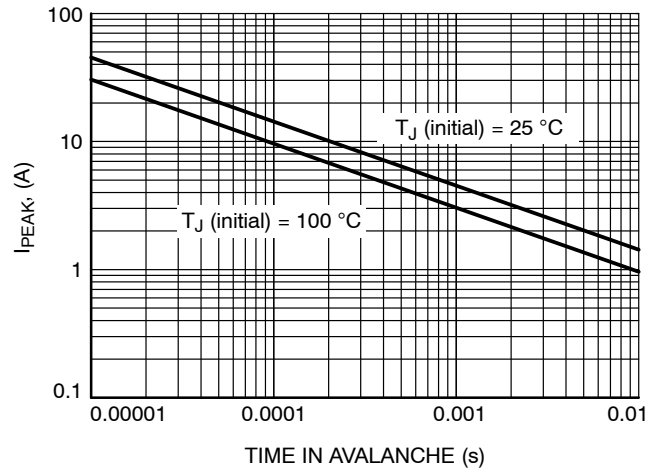


Figure 12. IPEAK vs. Time in Avalanche

NVMFS5H663NL, NVMFS5H663NLWF

TYPICAL CHARACTERISTICS (continued)

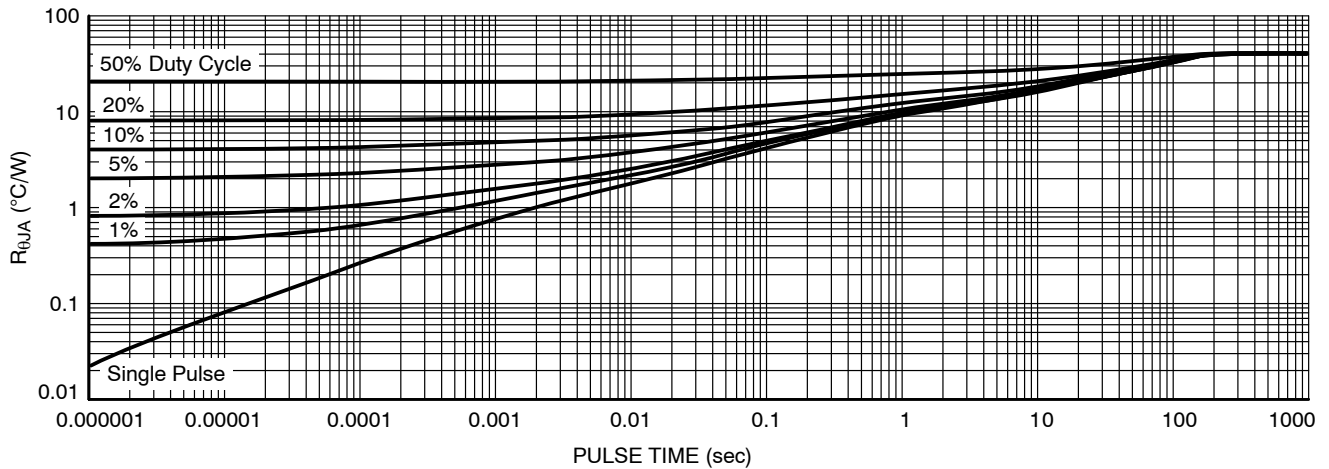


Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

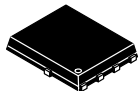
Device	Marking	Package	Shipping†
NVMFS5H663NLT1G	5H663L	DFN5 (Pb-Free)	1,500 / Tape & Reel
NVMFS5H663NLWFT1G	663LWF	DFNW5 (Pb-Free, Wettable Flanks)	1,500 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

NVMFS5H663NL, NVMFS5H663NLWF

REVISION HISTORY

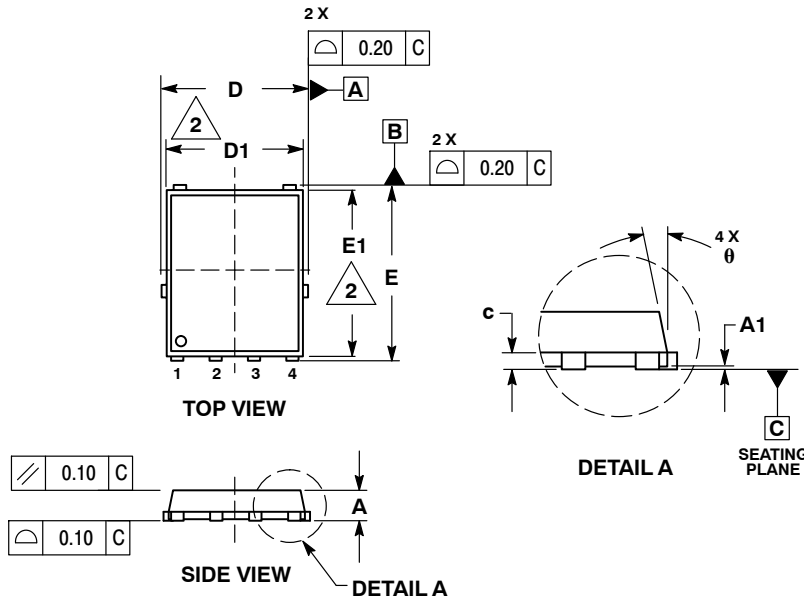
Revision	Description of Changes	Date
3	Rebranded the Data Sheet to onsemi format.	10/20/2025
4	Revision to add case outline 507BA in the data sheet.	10/22/2025



1
SCALE 2:1

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018

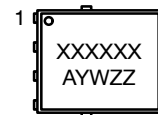


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

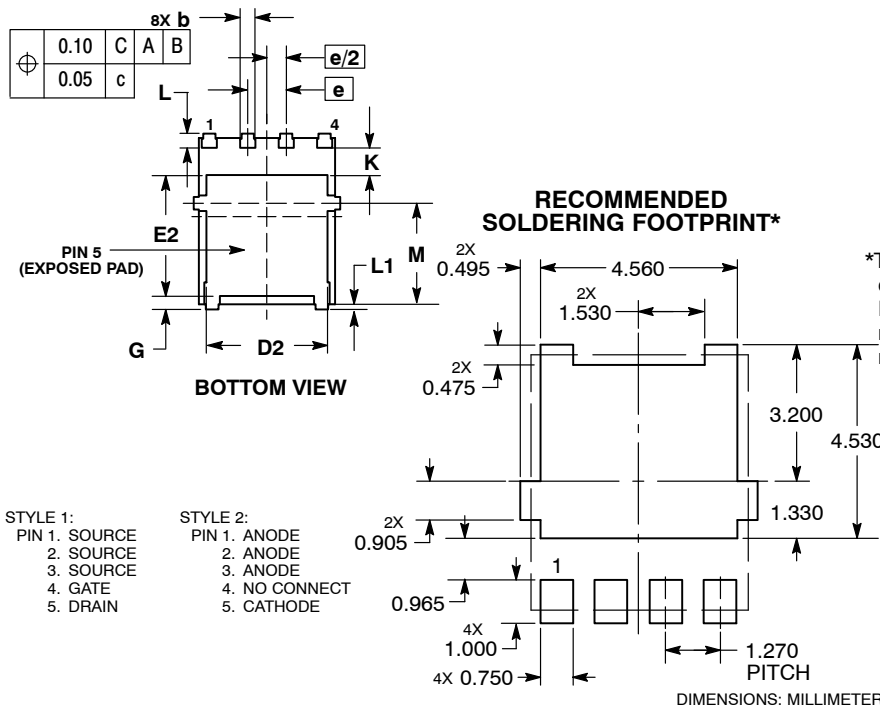
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°

GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

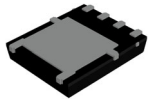


- STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
- STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

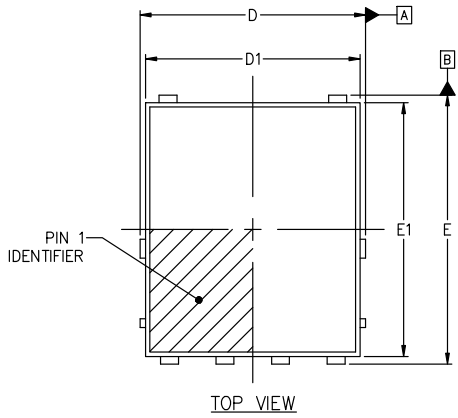
DOCUMENT NUMBER:	98AON14036D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)	PAGE 1 OF 1

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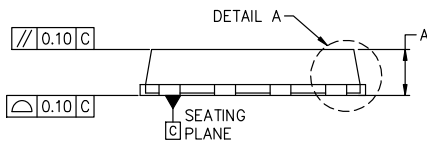


DFNW5 4.90x5.90x1.00, 1.27P
CASE 507BA
ISSUE C

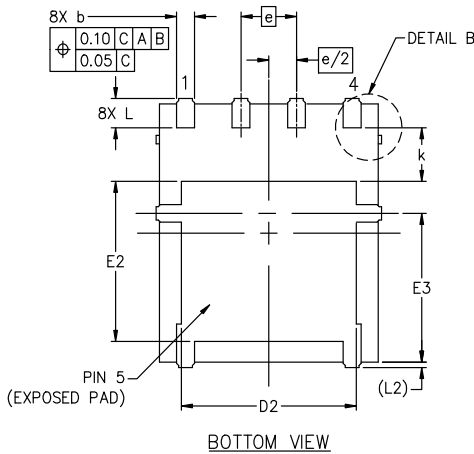
DATE 19 SEP 2024



TOP VIEW



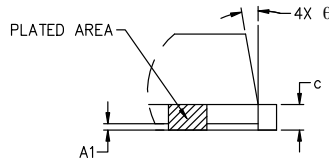
SIDE VIEW



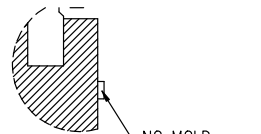
BOTTOM VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5M-2018.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.

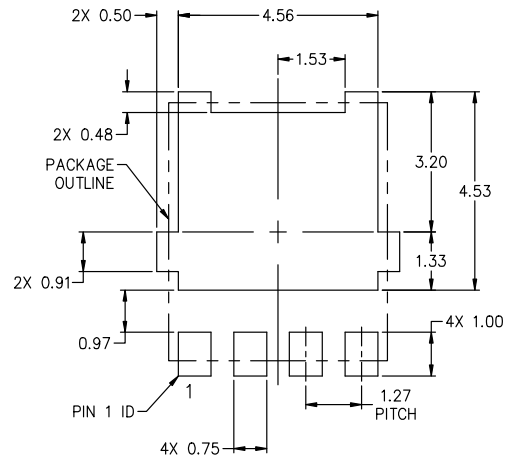


DETAIL "A"
SCALE 2:1



DETAIL "B"
SCALE 2:1

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
E3	3.00	3.40	3.80
e	1.27 BSC		
k	1.20	1.35	1.50
L	0.51	0.57	0.71
L2	0.15 REF.		
theta	0°	6°	12°



RECOMMENDED MOUNTING FOOTPRINT*
*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	DFNW5 4.90x5.90x1.00, 1.27P	PAGE 1 OF 1

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- ✓ Shortage Management
- ✓ Alternative Solution
- ✓ Excess Inventory Management